

SCHMITT INVERTER

The KIC7W14FK is high speed C²MOS SCHMITT INVERTER fabricated with silicon gate C²MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the C²MOS low power dissipation.

Pin configuration and function are the same as the KIC7WU04FK but the inputs have 25% V_{CC} hysteresis and with its schmitt trigger function, the KIC7W14FK can be used as a line receivers which will receive slow input signals.

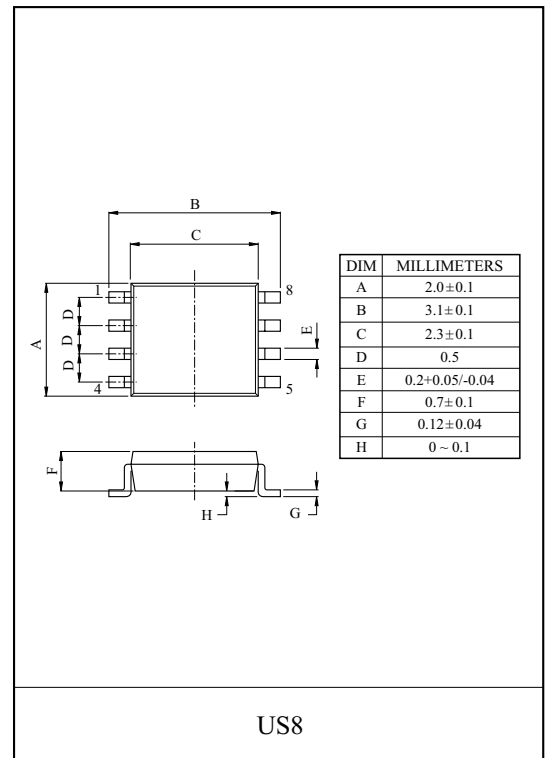
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES

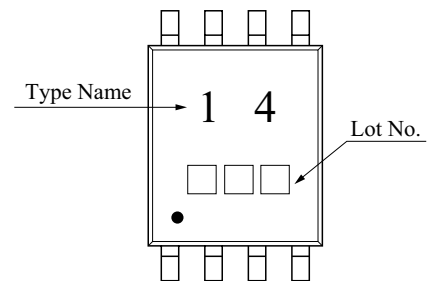
- High Speed : $t_{pd}=1\text{ns(Typ.)}$ at $V_{CC}=5\text{V}$.
- Low Power Dissipation : $I_{CC}=1\mu\text{A(Max.)}$ at $T_a=25^\circ\text{C}$.
- High Noise Immunity : $V_H=1.1\text{V}$ at $T_a=25^\circ\text{C}$
- Output Drive Capability : 10 LSTTL Loads.
- Symmetrical Output Impedance : $|I_{OH}|=|I_{OL}|=4\text{mA(Min.)}$
- Balanced Propagation Delays : $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range : $V_{CC(opr)}=2 \sim 6\text{V}$.

MAXIMUM RATINGS (T_a=25 °C)

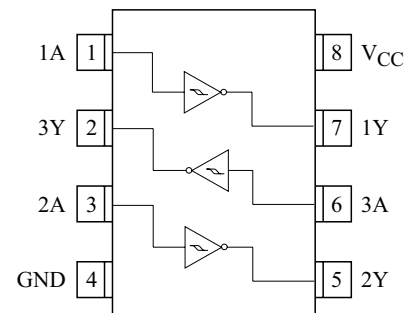
CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V _{CC}	-0.5 ~ 7	V
DC Input Voltage	V _{IN}	-0.5 ~ V _{CC} +0.5	V
DC Output Voltage	V _{OUT}	-0.5 ~ V _{CC} +0.5	V
Input Diode Current	I _{IK}	±20	mA
Output Diode Current	I _{OK}	±20	mA
DC Output Current	I _{OUT}	±25	mA
DC V _{CC} /Ground Current	I _{CC}	±25	mA
Power Dissipation	P _D	200	mW
Storage Temperature	T _{stg}	-65 ~ 150	°C
Lead Temperature (10s)	T _L	260	°C



MARKING

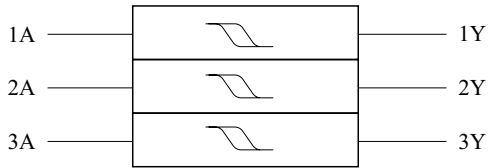


PIN CONNECTION (TOP VIEW)



KIC7W14FK

LOGIC DIAGRAM



TRUTH TABLE

A	Y
L	H
H	L

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	2 ~ 6	V
Input Voltage	V_{IN}	0 ~ V_{CC}	V
Output Voltage	V_{OUT}	0 ~ V_{CC}	V
Operating Temperature	T_{opr}	-40 ~ 85	°C

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION	$T_a=25\text{ }^\circ\text{C}$				$T_a=-40\text{ }^\circ\text{C} \sim 85\text{ }^\circ\text{C}$		UNIT	
			V_{CC}	MIN.	TYP.	MAX.	MIN.	MAX.		
Positive Threshold Voltage	V_P	-	2.0	1.0	1.25	1.5	1.0	1.5	V	
			4.5	2.3	2.7	3.15	2.3	3.15		
			6.0	3.0	3.5	4.2	3.0	4.2		
Negative Threshold Voltage	V_N	-	2.0	0.3	0.65	0.9	0.3	0.9	V	
			4.5	1.13	1.6	2.0	1.13	2.0		
			6.0	1.5	2.3	2.6	1.5	2.6		
Hysteresis Voltage	V_H	-	2.0	0.3	0.6	1.0	0.3	1.0	V	
			4.5	0.6	1.1	1.4	0.6	1.4		
			6.0	0.8	1.2	1.7	0.8	1.7		
High-Level Output Voltage	V_{OH}	$V_{IN}=V_{IL}$	$I_{OH}=-20\text{ }\mu\text{A}$	2.0	1.9	2.0	-	1.9	-	V
				4.5	4.4	4.5	-	4.4	-	
				6.0	5.9	6.0	-	5.9	-	
			$I_{OH}=-4\text{ mA}$ $I_{OH}=-5.2\text{ mA}$	4.5	4.18	4.31	-	4.13	-	
				6.0	5.68	5.80	-	5.63	-	
				6.0	-	-	-	-	-	
Low-Level Output Voltage	V_{OL}	$V_{IN}=V_{IH}$	$I_{OL}=20\text{ }\mu\text{A}$	2.0	-	0.0	0.1	-	0.1	V
				4.5	-	0.0	0.1	-	0.1	
				6.0	-	0.0	0.1	-	0.1	
			$I_{OL}=4\text{ mA}$ $I_{OL}=5.2\text{ mA}$	4.5	-	0.17	0.26	-	0.33	
				6.0	-	0.18	0.26	-	0.33	
				6.0	-	-	-	-	-	
Input Leakage Current	I_{IN}	$V_{IN}=V_{CC}$ or GND	6.0	-	-	± 0.1	-	± 1.0	μA	
Quiescent Supply Current	I_{CC}	$V_{IN}=V_{CC}$ or GND	6.0	-	-	1.0	-	10.0		

KIC7W14FK

AC ELECTRICAL CHARACTERISTICS (C_L=15pF, V_{CC}=5V, Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	Ta=25 °C			UNIT
			MIN.	TYP.	MAX.	
Output Transition Time	t _{TLH}	-	-	4	8	ns
	t _{THL}					
Propagation Delay Time	t _{pLH}	-	-	11	21	ns
	t _{pHL}					

AC ELECTRICAL CHARACTERISTICS (C_L=50pF, Input t_r=t_f=6ns)

CHARACTERISTIC	SYMBOL	TEST CONDITION	V _{CC}	Ta=25 °C			Ta=-40 ~ 85 °C		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	t _{TLH} t _{THL}	-	2.0	-	30	75	-	95	ns
			4.5	-	8	15	-	19	
			6.0	-	7	13	-	16	
Propagation Delay Time	t _{pLH} t _{pHL}	-	2.0	-	42	125	-	155	ns
			4.5	-	14	25	-	31	
			6.0	-	12	21	-	26	
Input Capacitance	C _{IN}	-	-	5	10	-	10	pF	
Power Dissipation Capacitance	C _{PD}	(Note 1)	-	28	-	-	-		

Note 1 : C_{PD} is defined as the value of internal equivalent capacitance of IC which is calculated from the operating current consumption without load (refer to Test Circuit.) Average operating current can be obtained by the equation hereunder.

$$I_{CC(opp)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2 \text{ (per gate)}$$